

Supporting information

Insights into the photocatalytic mechanism of g- C₃N₄/Cs₂BBr₆ (B = Pt, Sn, Ti) heterojunction photocatalysts by density functional theory calculations

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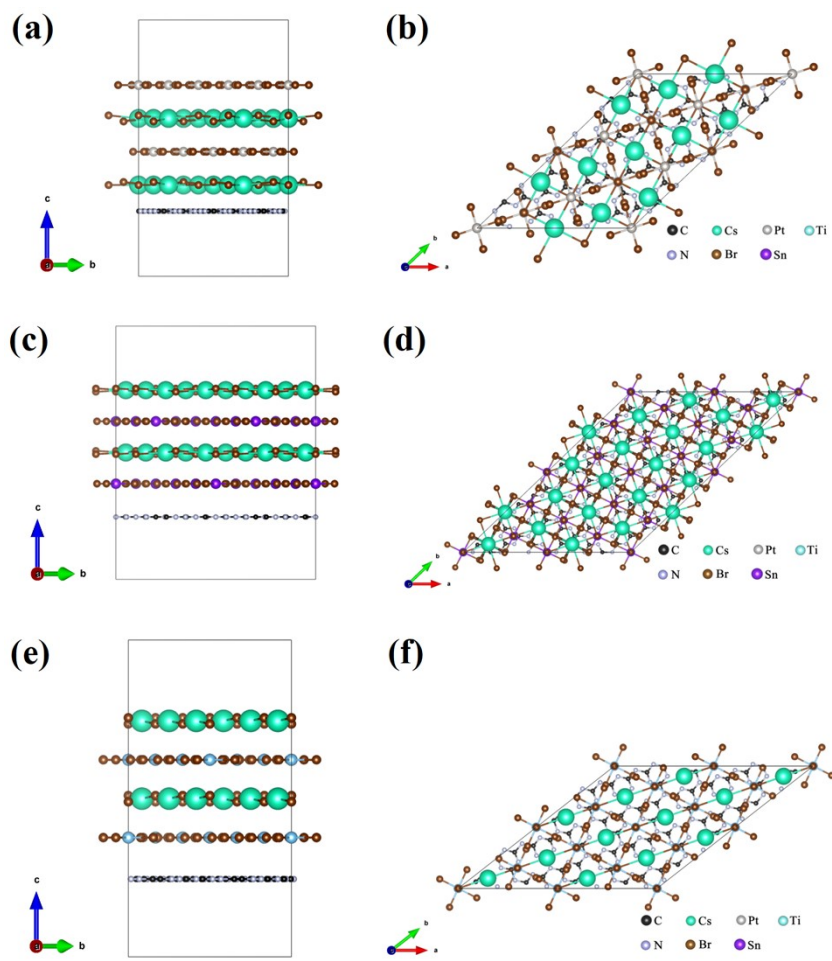


Fig. S1 Theoretical models for (a, b) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{PtBr}_6$, (c, d) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{SnBr}_6$, and (e, f) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{TiBr}_6$ heterojunctions.

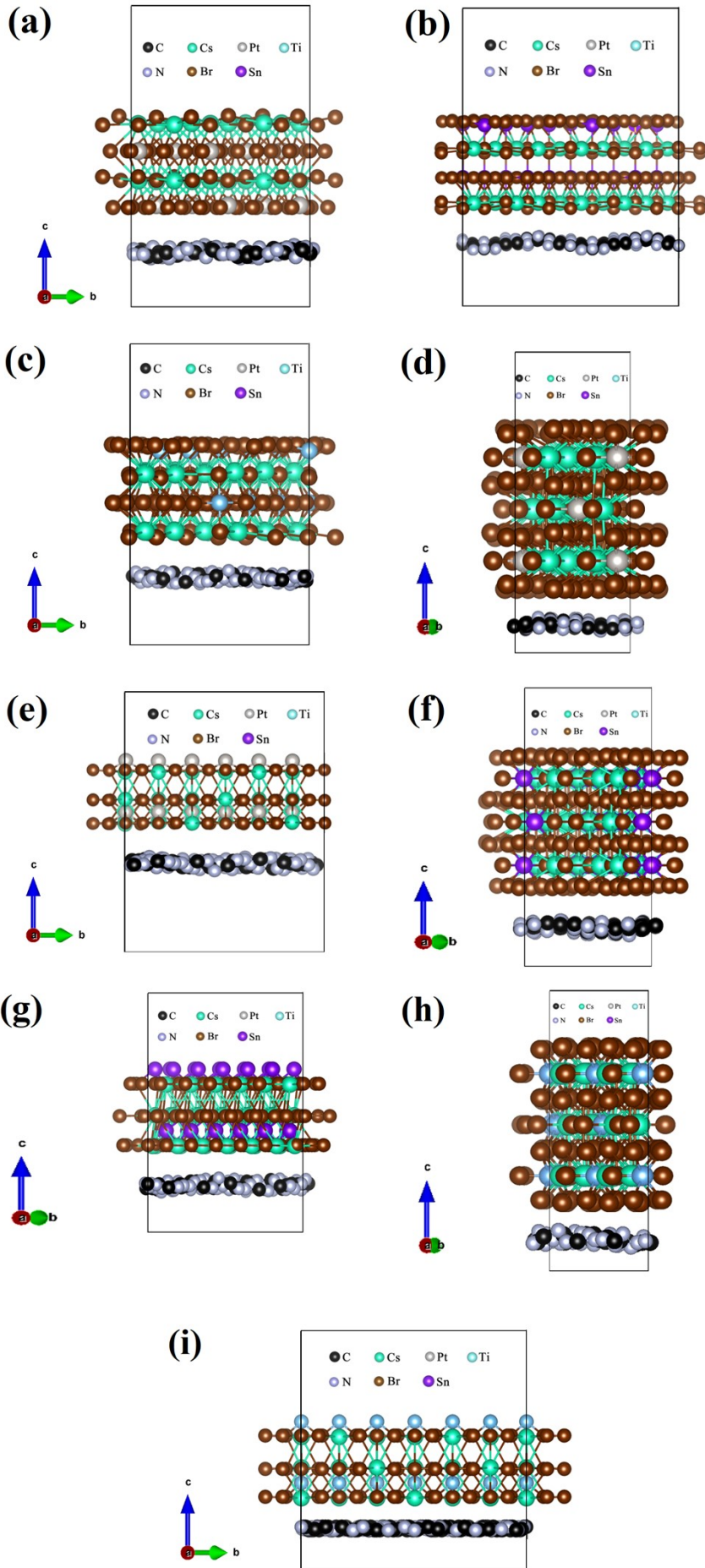


Fig. S2 Optimized geometric structures of (a) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{PtBr}_6(001)$ heterostructure with Pt-terminated surface, (b) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{SnBr}_6(001)$ heterostructure with Cs-terminated surface, (c) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{TiBr}_6(001)$ heterostructure with Cs-terminated surface, (d) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{PtBr}_6(110)$ heterostructure, (e) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{PtBr}_6(111)$ heterostructure, (f) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{SnBr}_6(110)$ heterostructure, (g) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{SnBr}_6(111)$ heterostructure, (h) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{TiBr}_6(110)$ heterostructure and (i) $g\text{-C}_3\text{N}_4/\text{Cs}_2\text{TiBr}_6(111)$ heterostructure.

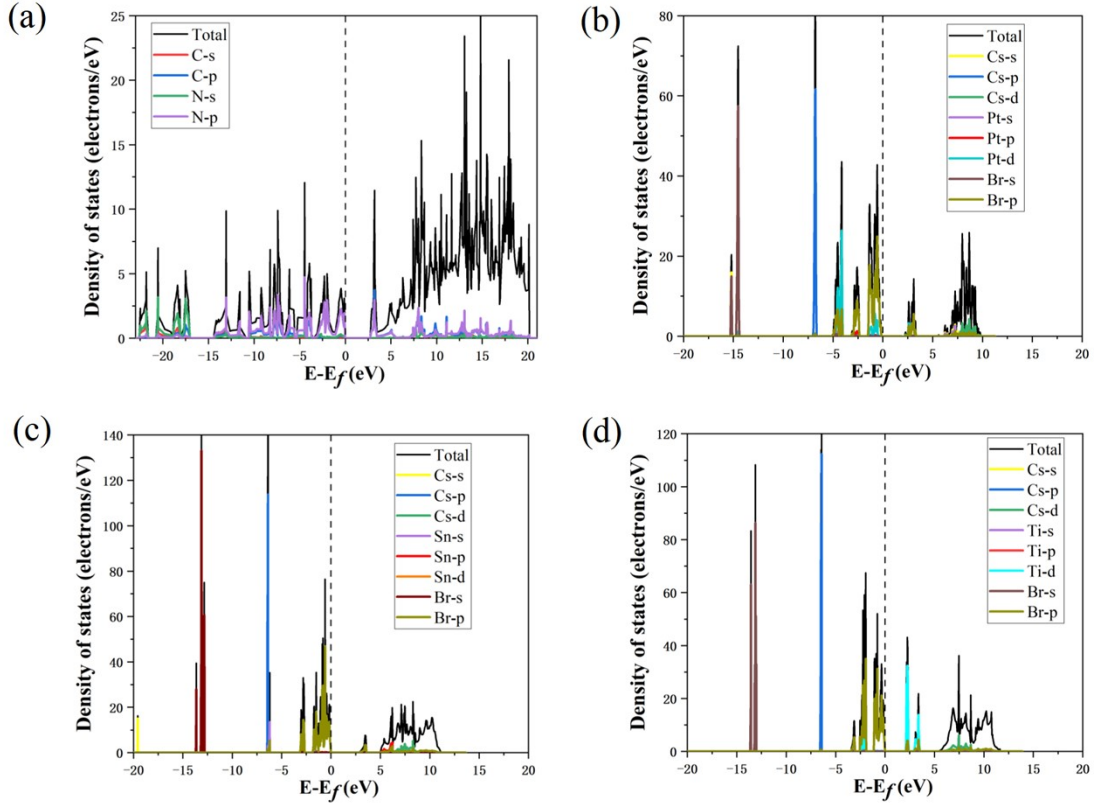


Fig. S3 Calculated TDOS and PDOS of (a) monolayer $g\text{-C}_3\text{N}_4$, (b) $\text{Cs}_2\text{PtBr}_6(001)$ slab, (c) $\text{Cs}_2\text{SnBr}_6(001)$ slab, (d) $\text{Cs}_2\text{TiBr}_6(001)$ slab over a wider energy range (-20 eV to 20 eV). The black vertical line is Fermi level.

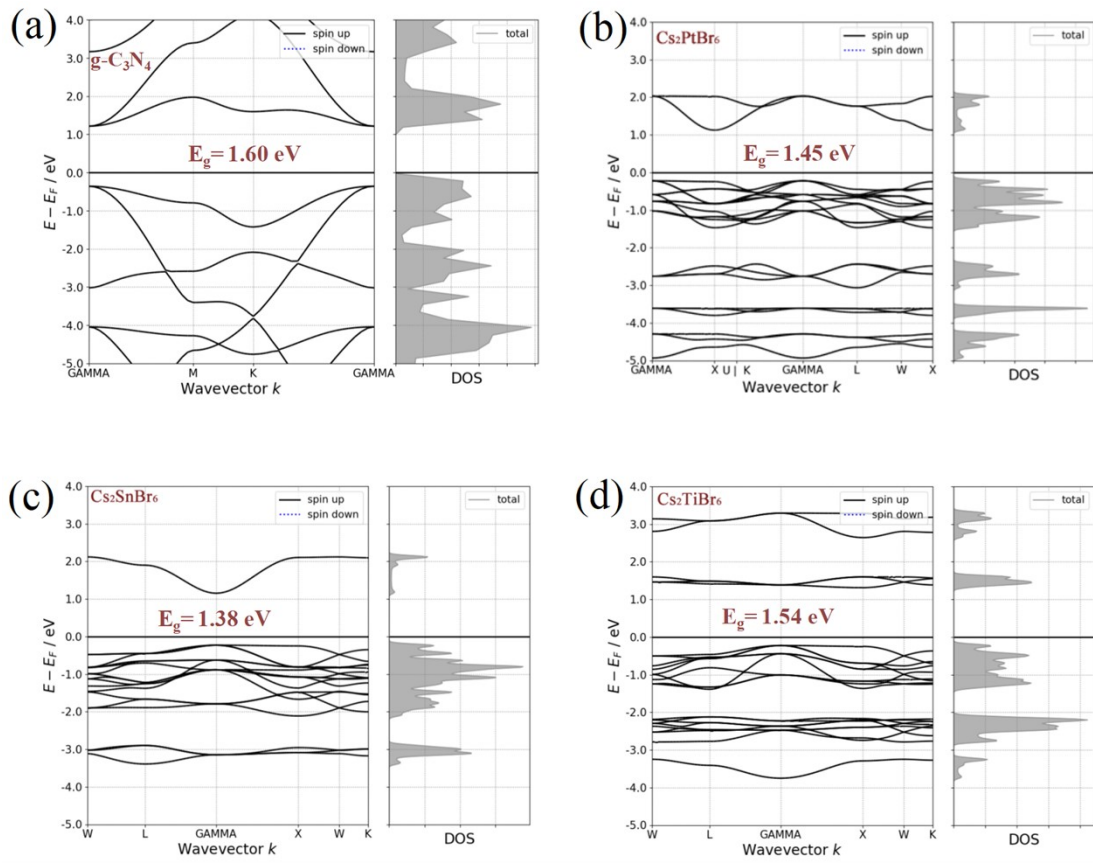


Fig. S4 Band structures and density of states of the (a) $g\text{-C}_3\text{N}_4$, (b) Cs_2PtBr_6 , (c) Cs_2SnBr_6 , (d) Cs_2TiBr_6 calculated by PBE functional.

Table. S1 Binding energies (eV) of g-C₃N₄/Cs₂PtBr₆ heterojunctions with varying Cs₂PtBr₆ components.

Species	(001) plane	(110) plane	(111) plane	Pt-terminated
Binding energy (eV)	-4.25	-3.86	-3.08	-3.82
Mismatch energy (eV)	4.15	4.22	4.65	4.47

Table. S2 Binding energies (eV) of g-C₃N₄/Cs₂SnBr₆ heterojunctions with varying Cs₂SnBr₆ components.

Species	(001) plane	(110) plane	(111) plane	Cs- terminated
Binding energy (eV)	-1.65	-1.01	-1.50	-1.60
Mismatch energy (eV)	10.26	11.28	10.36	10.31

Table. S3 Binding energies (eV) of g-C₃N₄/Cs₂TiBr₆ heterojunctions with varying Cs₂TiBr₆ components.

Species	(001) plane	(110) plane	(111) plane	Cs- terminated
Binding energy (eV)	-2.88	-2.27	-2.00	-2.80
Mismatch energy (eV)	6.26	6.66	7.05	6.35

Table. S4 Average Bader atomic charge (e), the minimum distance (Min dist. (Å)), and valency in isolated Cs₂PtBr₆ and g-C₃N₄.

Atom	C	N	Cs	Pt	Br
Average Bader charge (e)	0.64	7.47	8.04	9.52	7.55
Valency	3.36	-2.47	0.96	0.48	-0.55

Table. S5 Average Bader atomic charge (e), the minimum distance (Min dist. (Å)), and valency in isolated Cs₂SnBr₆ and g-C₃N₄.

Atom	C	N	Cs	Sn	Br
Average Bader charge (e)	0.88	7.20	8.01	11.92	7.90
Valency	3.12	-2.20	0.99	2.08	-0.90

Table. S6 Average Bader atomic charge (e), the minimum distance (Min dist. (Å)), and valency in isolated Cs₂TiBr₆ and g-C₃N₄.

Atom	C	N	Cs	Ti	Br
Average Bader charge (e)	0.94	7.17	8.01	7.89	7.94
Valency	3.06	-2.17	0.99	2.11	-0.94